N-Channel Enhancement Mode Power MOSFET

Description

The GT035N12TA uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

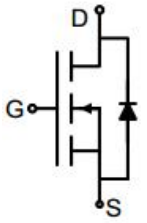
AEC-Q101Qualified

General Features

- V_{DS} 120V
- I_D (at V_{GS} = 10V) 180A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 3.8mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-220

Ordering Information

Device	Package	Marking	Packaging
GT035N12TA	TO-220	GT035N12	50pcs/Tube

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	120	V
Continuous Drain Current	T_C = 25ºC	I_D	180	A
	T_C = 100ºC		114	
Pulsed Drain Current (note1)		I_{DM}	720	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	230	W
Single pulse avalanche energy （note2）		E_{AS}	529	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	ºC/W
Maximum Junction-to-Case	R_{thJC}	0.54	ºC/W

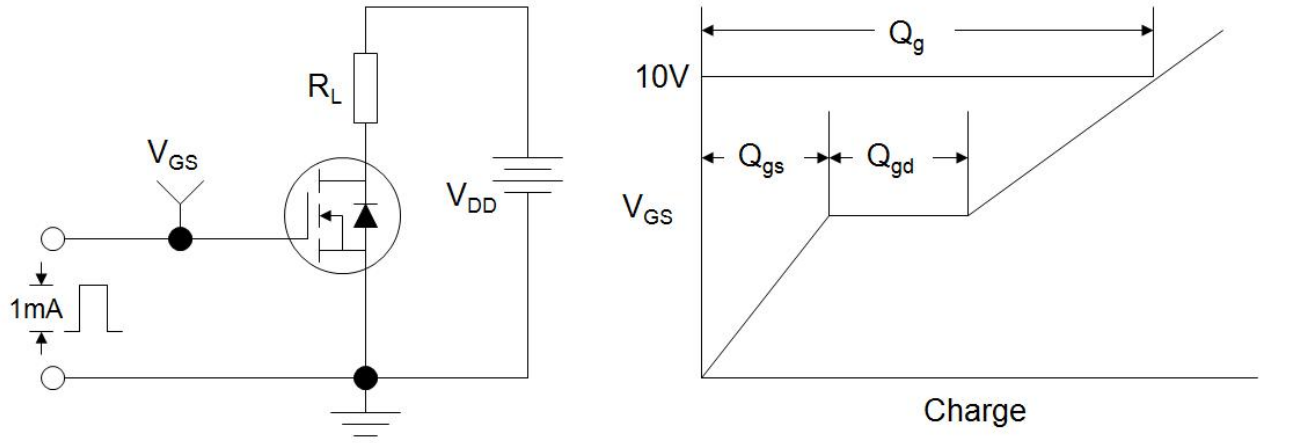
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	120	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 120V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	3.0	4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 50A	--	3.1	3.8	mΩ
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 50A	--	55	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 60V, f = 0.5MHz	--	8335	--	pF
Output Capacitance	C_{oss}		--	860	--	
Reverse Transfer Capacitance	C_{rss}		--	7	--	
Total Gate Charge	Q_g	V_{DD} = 60V, I_D = 50A, V_{GS} = 10V	--	126	--	nC
Gate-Source Charge	Q_{gs}		--	38	--	
Gate-Drain Charge	Q_{gd}		--	31	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 60V, I_D = 50A, R_G = 4.7Ω	--	26	--	ns
Turn-on Rise Time	t_r		--	84	--	
Turn-off Delay Time	$t_{d(off)}$		--	54	--	
Turn-off Fall Time	t_f		--	18	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	180	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 50A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 50A, V_{GS} = 0V di/dt=100A/us	--	176	--	nC
Reverse Recovery Time	Trr		--	79	--	ns

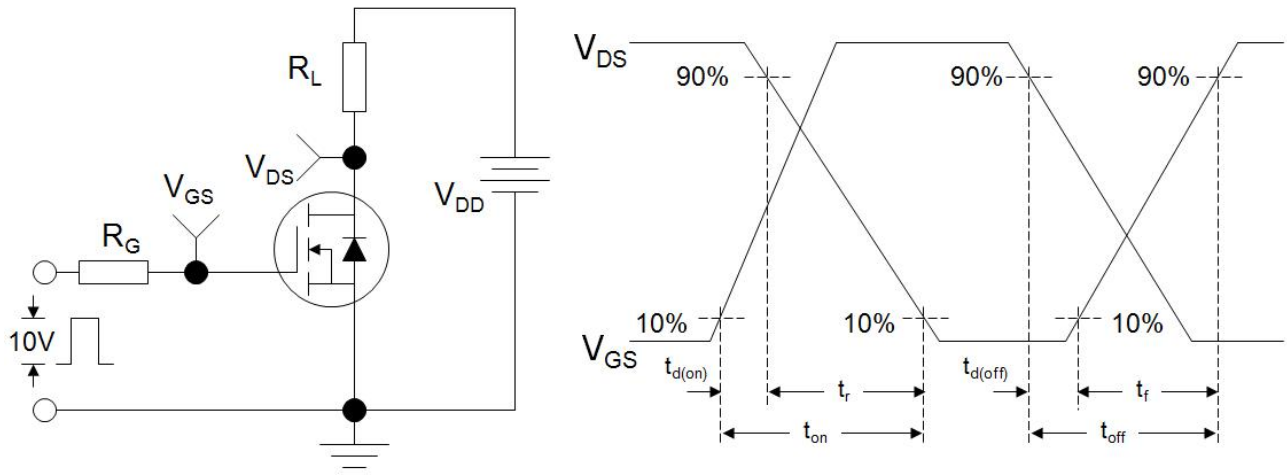
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 1444mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

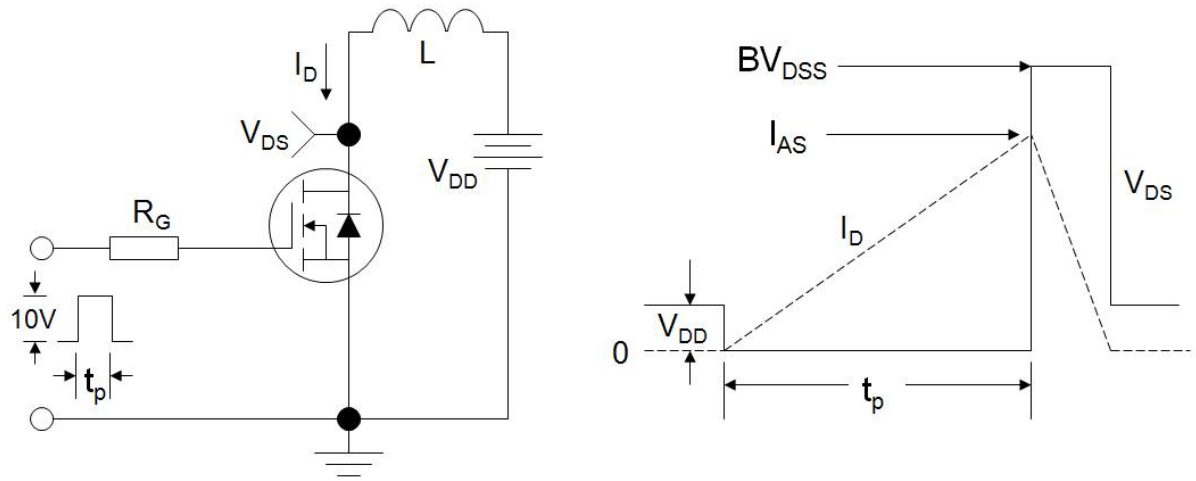
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

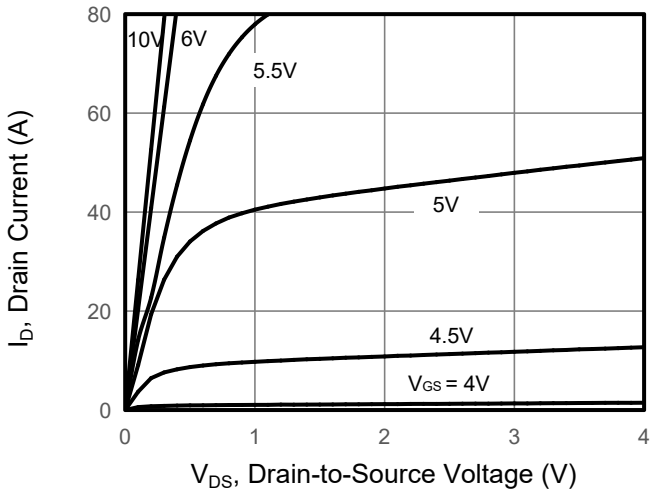


Figure 2. Transfer Characteristics

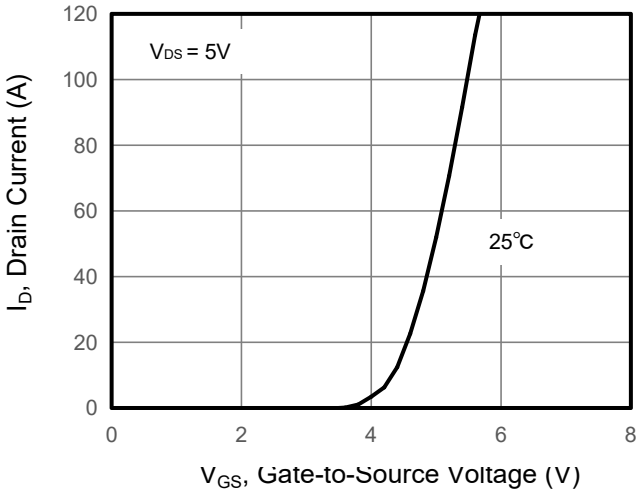


Figure 3. Drain Source On Resistance

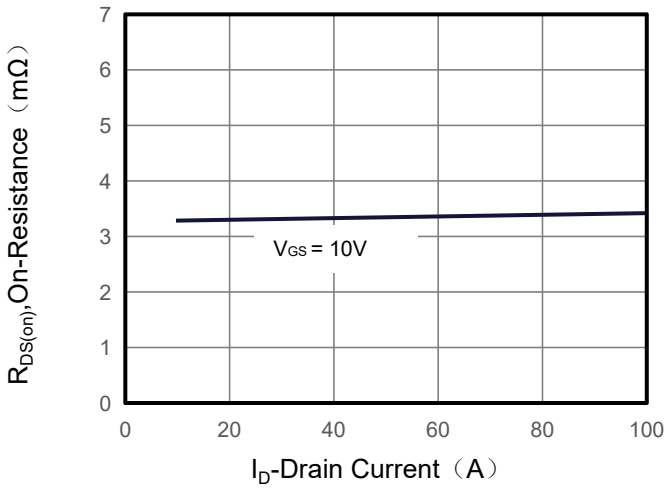


Figure 4. Gate Charge

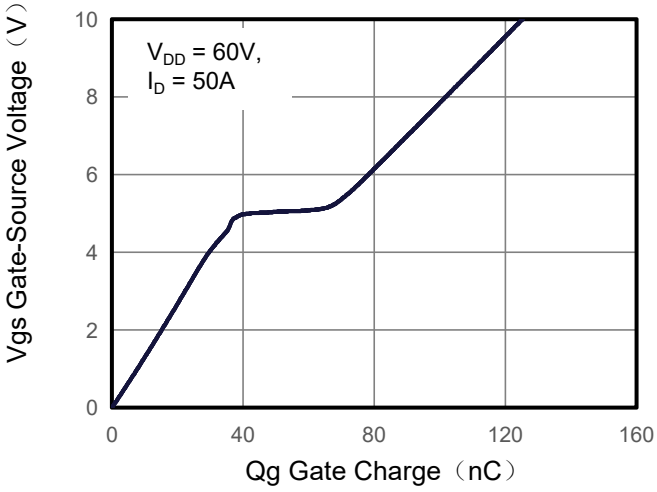


Figure 5. Capacitance

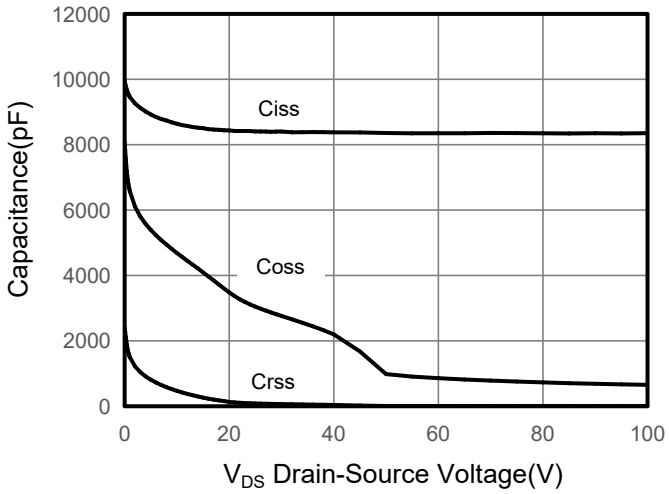
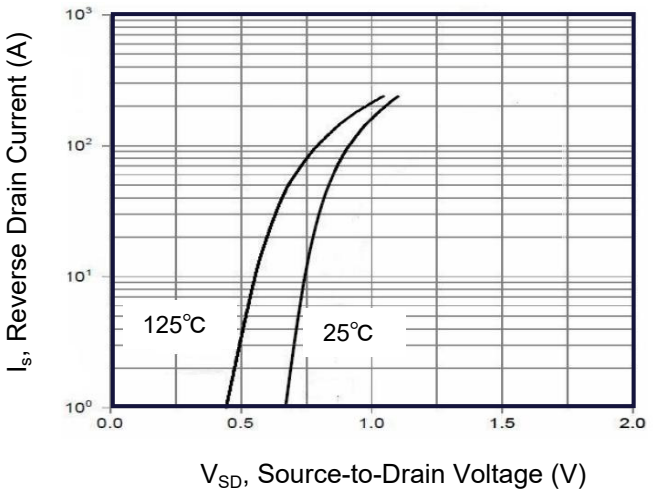


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

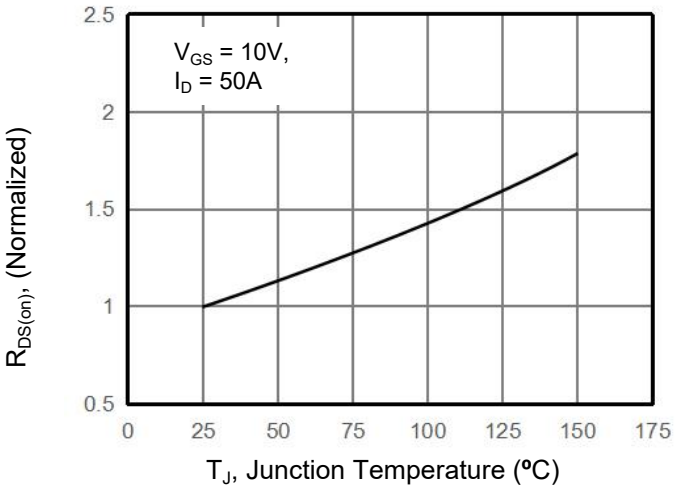


Figure 8. Safe Operation Area

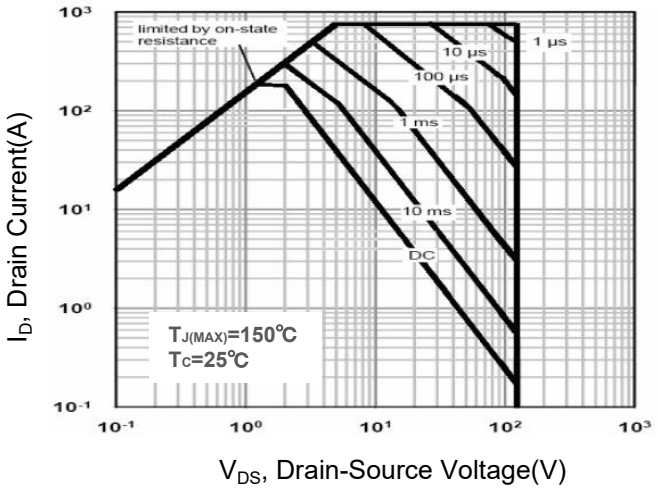


Figure 9. Maximum Continuous Drain Current vs Case Temperature

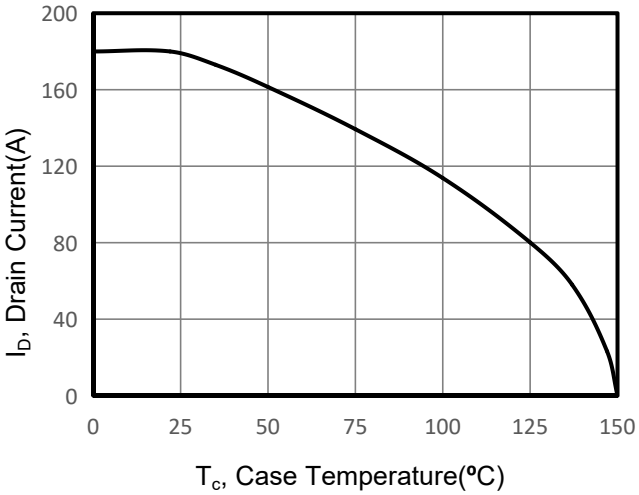
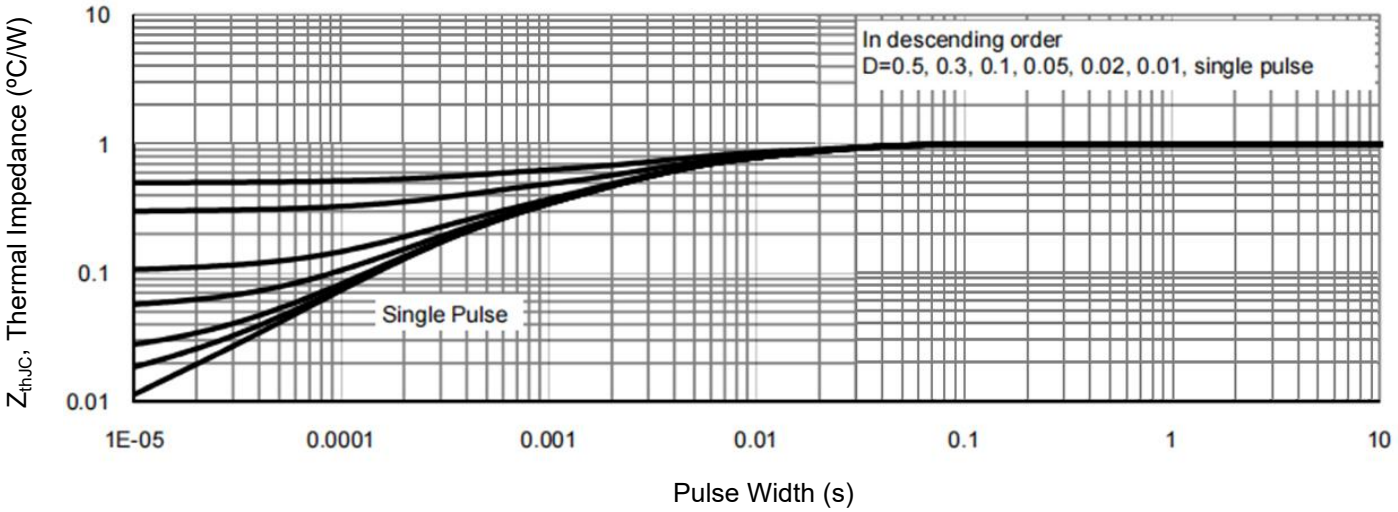
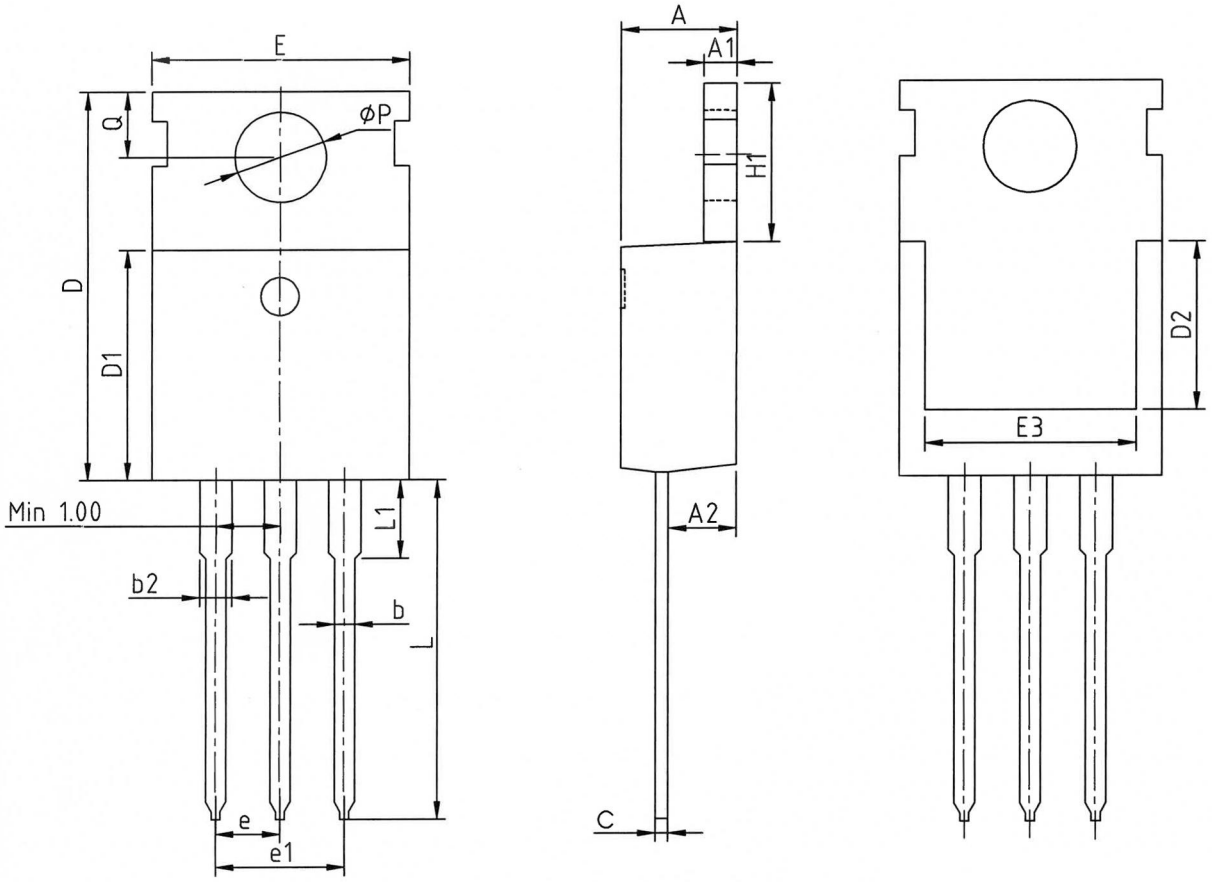


Figure 10. Normalized Maximum Transient Thermal Impedance



TO-220 Package Information



COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX
A	4.37	4.57	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	6.30	7.10
E	9.70	10.00	10.30
E3	7.00	7.80	8.60
e		2.54 BSC	
e1		5.08 BSC	
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00